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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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OK
8/2/01

In Re U.S. Patent Application)
)
Applicant: Kozo NAKAMURA, Toshiaki)
SAISHOJI, Hirotaka NAKAJIMA,)
Shinya SADOHARA, Masashi)
NISHIMURA, Toshirou KOTOOKA,)
AND Yoshiyuki SHIMANUKI)
)
Serial No.: Not Yet Assigned)
)
Filed: Herewith)
)
For: PRODUCTION METHOD FOR SILICON SINGLE)
CRYSTAL AND PRODUCTION DEVICE FOR)
SINGLE CRYSTAL INGOT, AND HEAT)
TREATING METHOD FOR SILICON SINGLE)
CRYSTAL WAFER)
)
)

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

This is a Preliminary Amendment for entry in the above-identified application.

In the Claims:

Please amend claims as follows:

A' 6/2/01
3. (amended) The method for producing a silicon single crystal ingot according to Claim 1, characterized in that said conditions (a) and (b) are adjusted by changing the pulling speed of the silicon single crystal ingot when the silicon single crystal ingot is produced by the Czochralski method.